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(54) Title: METHOD OF PROCESSING SEMICONDUCTOR WAFERS

(57) Abstract

A method of processing a semiconductor wafer comprises rough grinding the front and back surfaces of the wafer to quickly reduce the thickness of the wafer. The front and back surfaces are then lapped with a lapping slurry to further reduce the thickness of the wafer and reduce damage caused by the rough grinding. Lapping time is reduced by provision of the rough grinding step. The wafer is etched in a chemical etchant to further reduce the thickness of the wafer and the front surface of the wafer is polished using a polishing slurry to reduce the thickness of the wafer down to a predetermined final wafer thickness. A fine grinding step may be added to eliminate lapping and/or reduce polishing time.